

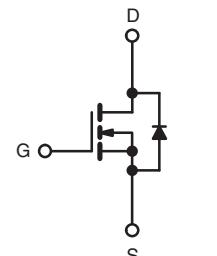
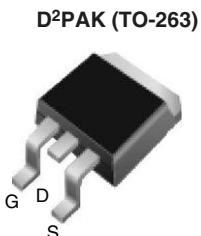
STB16PF06LT4-VB Datasheet

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Max)
60	0.032 at V _{GS} = 10 V	50	66 nC
	0.035 at V _{GS} = 4.5 V	40	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Logic-Level Gate Drive
- Fast Switching
- Compliant to RoHS Directive 2002/95/EC



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	60	
Gate-Source Voltage	V _{GS}	± 10	
Continuous Drain Current ^f	I _D	50	A
Continuous Drain Current		36	
Pulsed Drain Current ^a	I _{DM}	200	
Linear Derating Factor		1.0	W/°C
Linear Derating Factor (PCB Mount) ^e		0.025	
Single Pulse Avalanche Energy ^b	E _{AS}	400	mJ
Maximum Power Dissipation	P _D	150	W
Maximum Power Dissipation (PCB Mount) ^e		3.7	
Peak Diode Recovery dV/dt ^c	dV/dt	4.5	V/ns
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) ^d	for 10 s	300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V_{DD} = 25 V, starting T_J = 25 °C, L = 179 µH, R_g = 25 Ω, I_{AS} = 51 A (see fig. 12).
- I_{SD} ≤ 51 A, dI/dt ≤ 250 A/µs, V_{DD} ≤ V_{DS}, T_J ≤ 175 °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).
- Current limited by the package, (die current = 51 A).

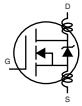
THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	$^{\circ}\text{C}/\text{W}$
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250 \mu\text{A}$		60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = 1 \text{ mA}$		-	0.070	-	$^{\circ}\text{C}/\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		1.0	-	3.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 10 \text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	25	μA
		$V_{DS} = 48 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 150^{\circ}\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 21 \text{ A}^b$	-	0.032	-	Ω
		$V_{GS} = 4.5 \text{ V}$	$I_D = 15 \text{ A}^b$	-	0.035	-	
Forward Transconductance	g_{fs}	$V_{DS} = 25 \text{ V}$, $I_D = 21 \text{ A}^b$		23	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1.0 \text{ MHz}$, see fig. 5		-	3000	-	pF
Output Capacitance	C_{oss}			-	1000	-	
Reverse Transfer Capacitance	C_{rss}			-	200	-	
Total Gate Charge	Q_g	$V_{GS} = 5.0 \text{ V}$	$I_D = 51 \text{ A}$, $V_{DS} = 48 \text{ V}$, see fig. 6 and 13 ^b	-	60	-	nC
Gate-Source Charge	Q_{gs}			-	10	-	
Gate-Drain Charge	Q_{gd}			-	40	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30 \text{ V}$, $I_D = 51 \text{ A}$, $R_g = 4.6 \Omega$, $R_D = 0.56 \Omega$, see fig. 10 ^b		-	17	-	ns
Rise Time	t_r			-	230	-	
Turn-Off Delay Time	$t_{d(off)}$			-	42	-	
Fall Time	t_f			-	110	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p-n junction diode		-	-	50 ^c	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	200	
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}\text{C}$, $I_S = 51 \text{ A}$, $V_{GS} = 0 \text{ V}^b$		-	-	2.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}$, $I_F = 51 \text{ A}$, $dl/dt = 100 \text{ A}/\mu\text{s}^b$		-	130	180	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.84	1.3	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
 b. Pulse width $\leq 300 \mu\text{s}$; duty cycle $\leq 2\%$.
 c. Current limited by the package, (Die Current = 51 A).

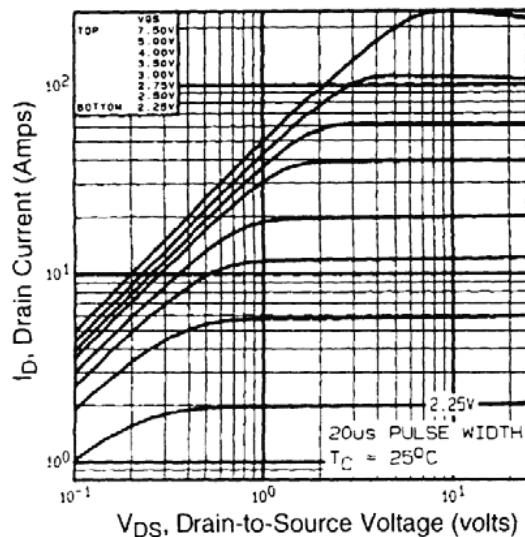
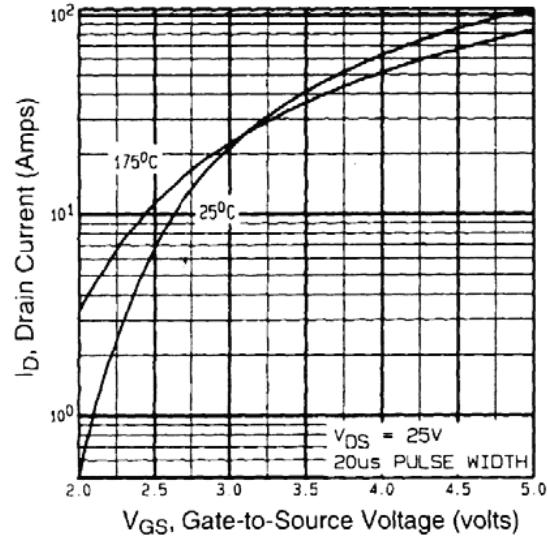
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)
Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^{\circ}\text{C}$ 

Fig. 3 - Typical Transfer Characteristics

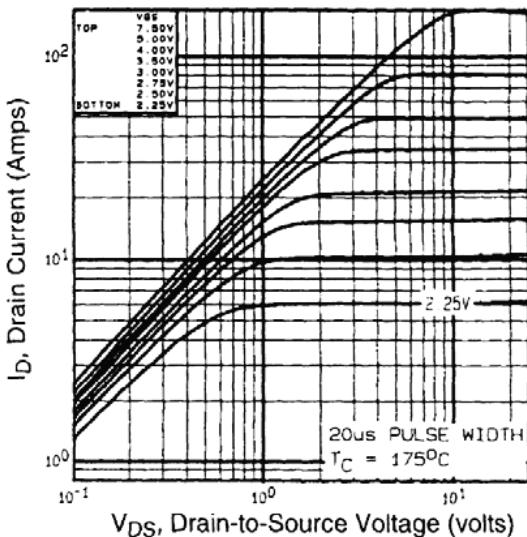
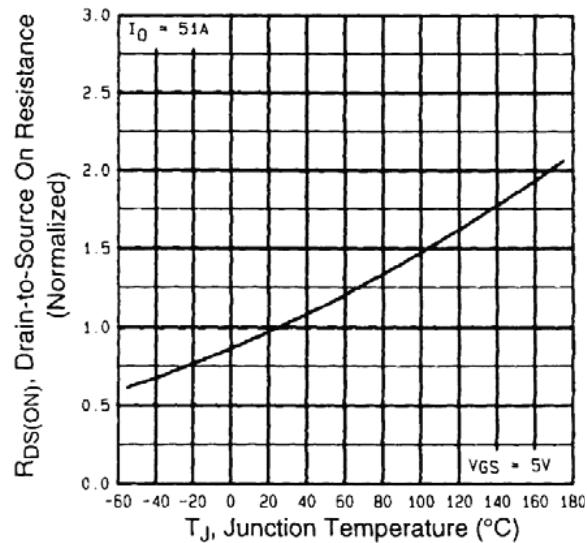
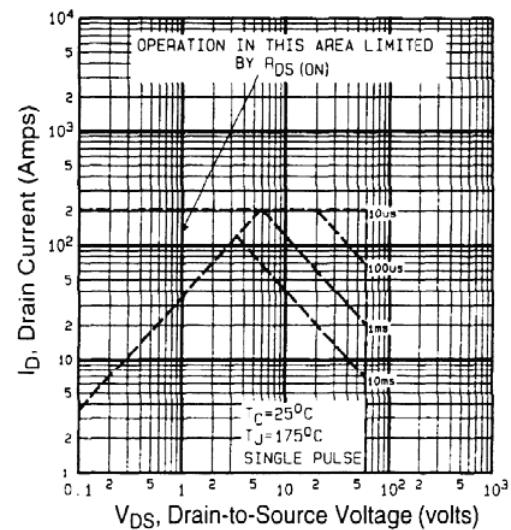
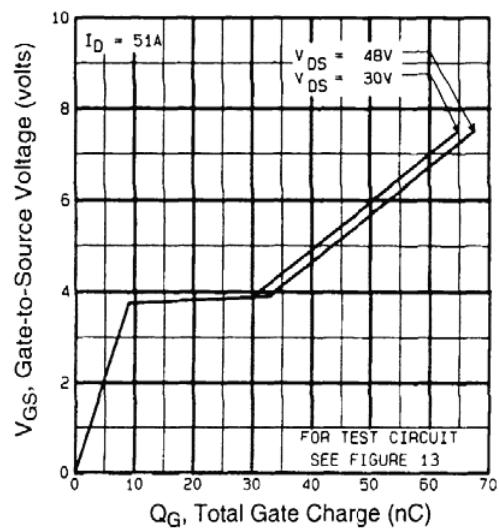
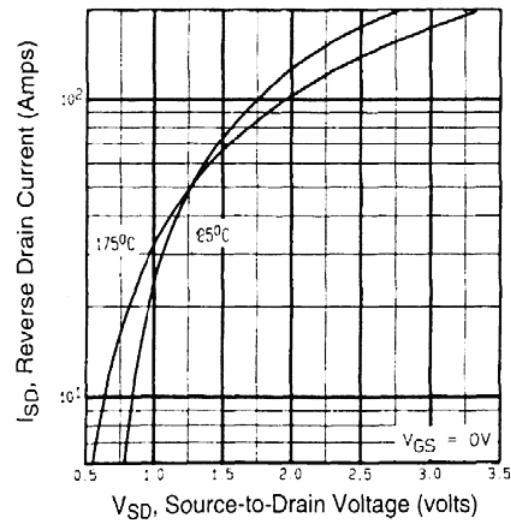
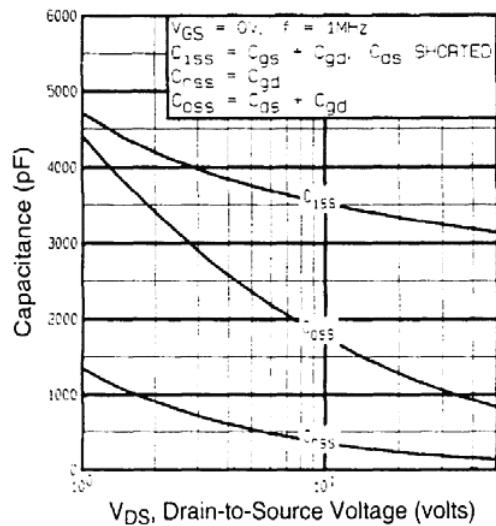
Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^{\circ}\text{C}$ 

Fig. 4 - Normalized On-Resistance vs. Temperature



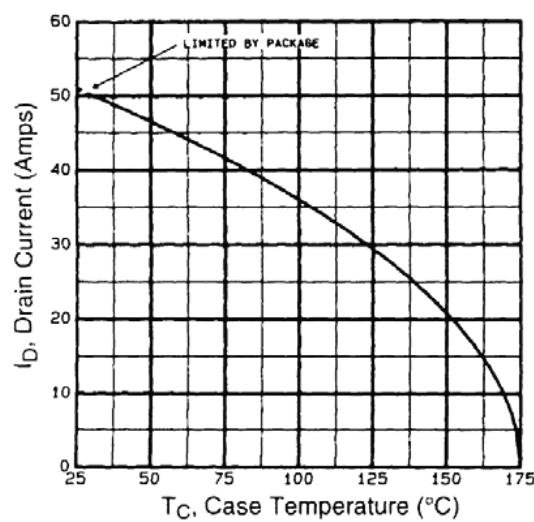


Fig. 9 - Maximum Drain Current vs. Case Temperature

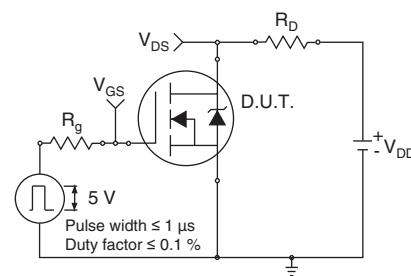


Fig. 10a - Switching Time Test Circuit

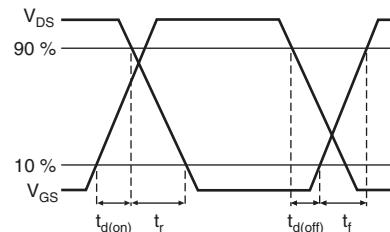


Fig. 10b - Switching Time Waveforms

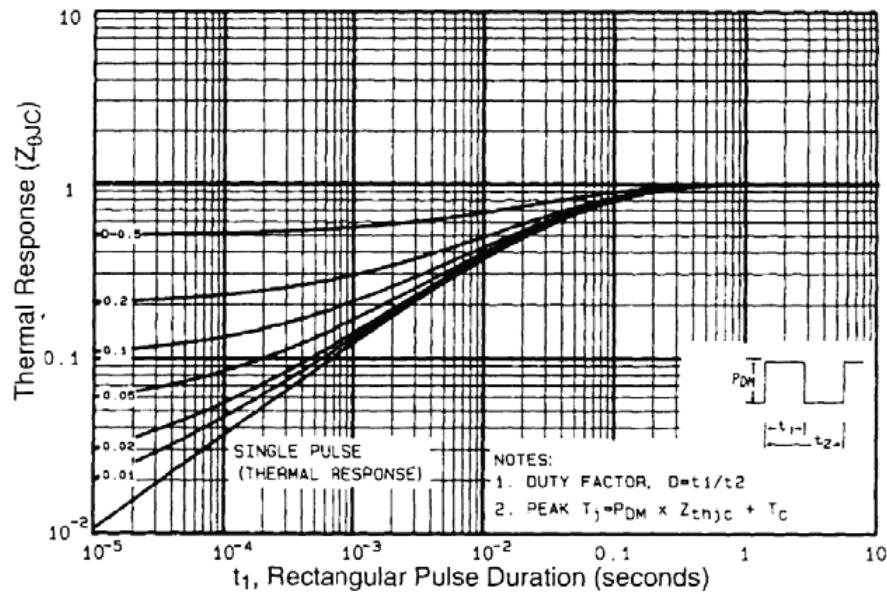


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

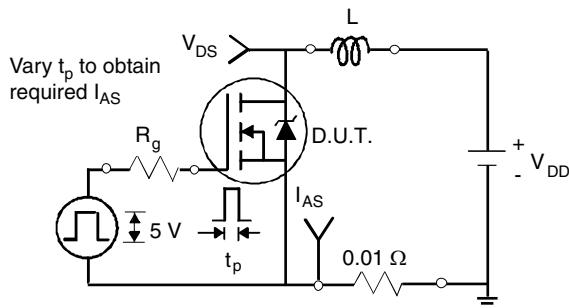


Fig. 12a - Unclamped Inductive Test Circuit

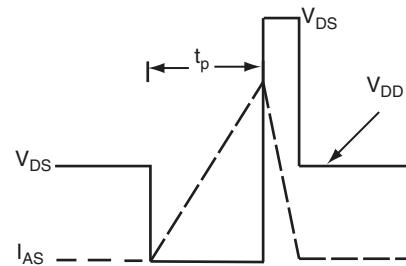


Fig. 12b - Unclamped Inductive Waveforms

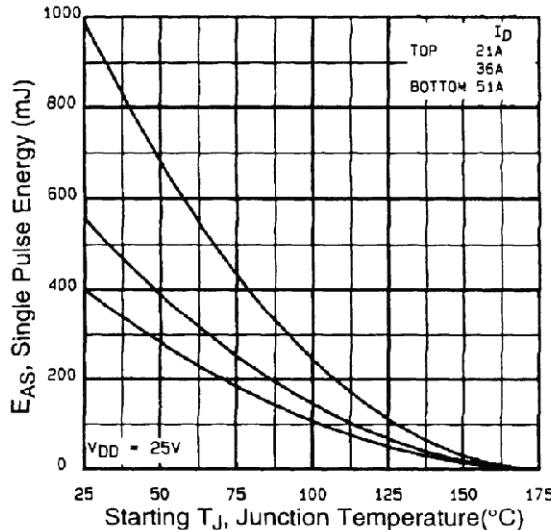


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

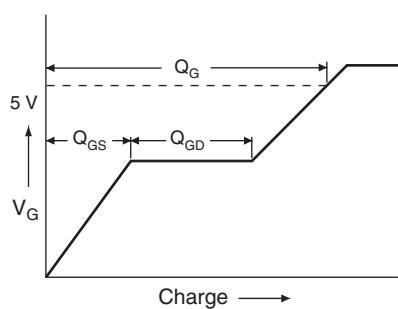


Fig. 13a - Basic Gate Charge Waveform

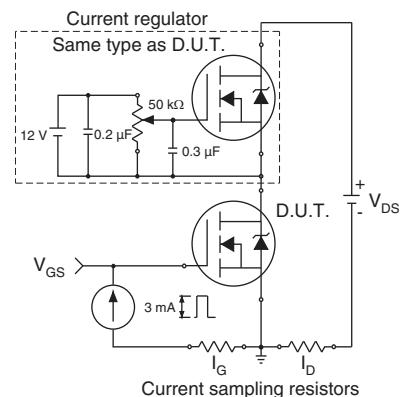
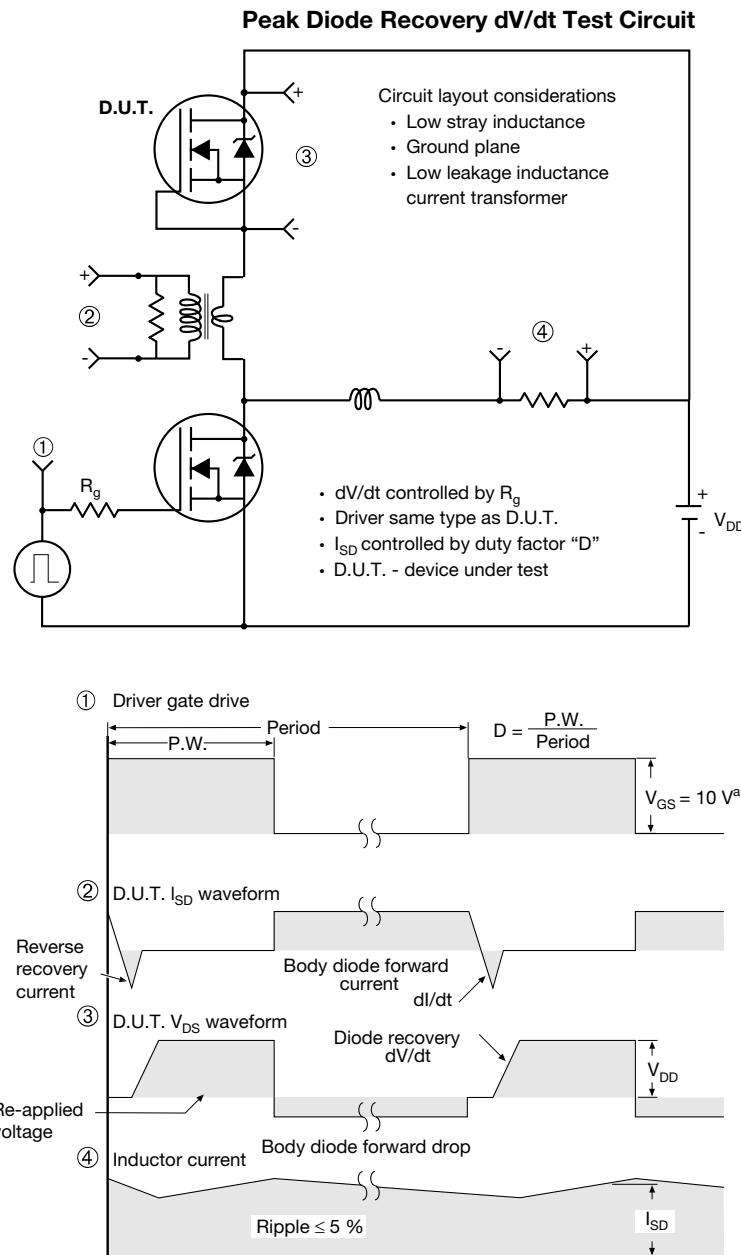
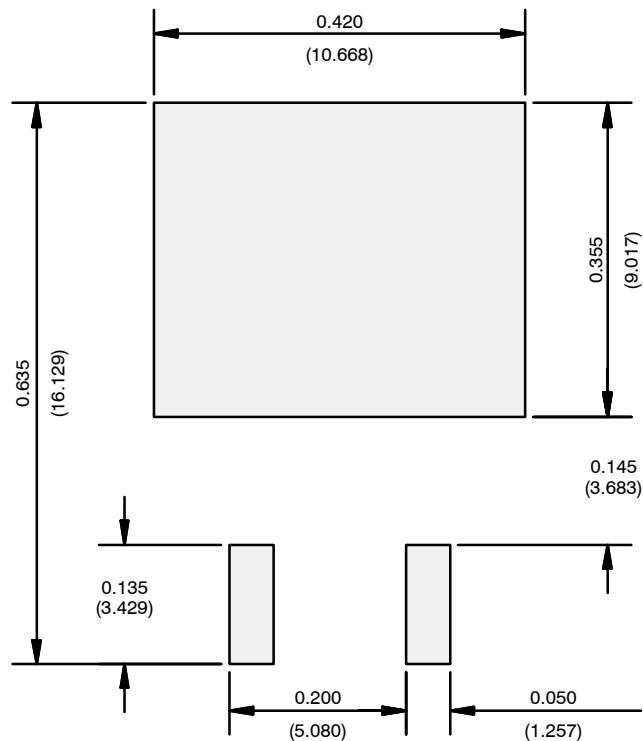


Fig. 13b - Gate Charge Test Circuit

**Fig. 14 - For N-Channel**

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead

Recommended Minimum Pads
Dimensions in Inches/(mm)

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